

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV-IRF5210S-T2
▶ Overseas	Part Number	IRF5210S
▶ Equivalent	Part Number	IRF5210S

"T2" means TO-263

EV is the abbreviation of name EVVO

- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

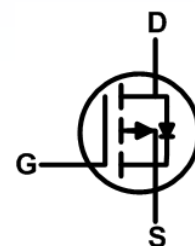
Description

The EV-IRF5210S-T2 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications. The EV-IRF5210S-T2 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
-100V	70mΩ	-25A

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-25	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10\text{V}^1$	-12	A
I_{DM}	Pulsed Drain Current ²	-75	A
EAS	Single Pulse Avalanche Energy ³	157.2	mJ
I_{AS}	Avalanche Current	18.9	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation ⁴	54	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.3	°C/W

P-Ch 100V Fast Switching MOSFETs

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-10A	---	58	70	mΩ
		V _{GS} =-4.5V, I _D =-8A	---	86	110	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.7	-2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-50	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-10A	---	24	---	S
Q _g	Total Gate Charge	V _{DS} =-50V, V _{GS} =-10V, I _D =-20A	---	44.5	---	nC
Q _{gs}	Gate-Source Charge		---	9.13	---	
Q _{gd}	Gate-Drain Charge		---	5.93	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-50V, V _{GS} =-10V, R _G =3.3Ω, I _D =-10A	---	12	---	ns
T _r	Rise Time		---	27.4	---	
T _{d(off)}	Turn-Off Delay Time		---	79	---	
T _f	Fall Time		---	53.6	---	
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	3029	---	pF
C _{oss}	Output Capacitance		---	129	---	
C _{rss}	Reverse Transfer Capacitance		---	76	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-25	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-8A, di/dt=-100A/μs, T _J =25°C	---	38.7	---	nS
Q _{rr}	Reverse Recovery Charge		---	22.4	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=-25V, V_{GS}=-10V, L=0.88mH, I_{AS}=-18.9A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

P-Ch 100V Fast Switching MOSFETs

Typical Characteristics

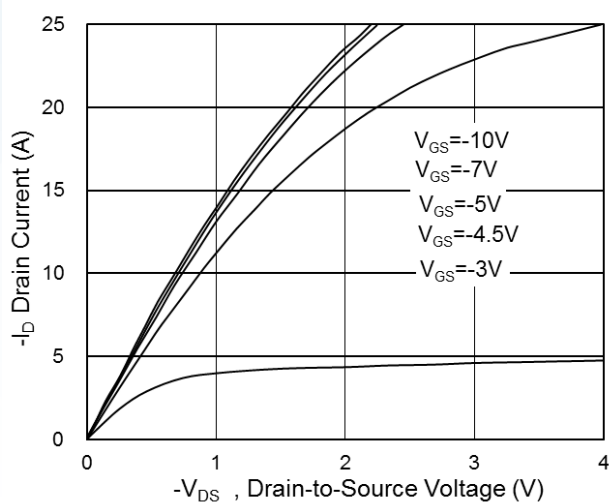


Fig.1 Typical Output Characteristics

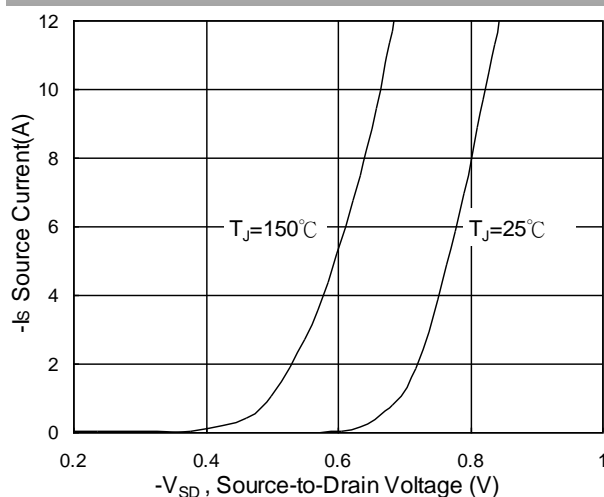


Fig.3 Typical S-D Diode Forward Voltage

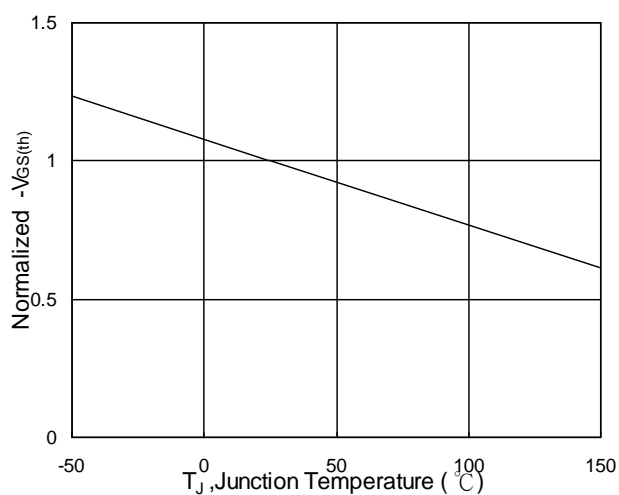


Fig.5 Normalized $V_{GS(th)}$ vs T_J

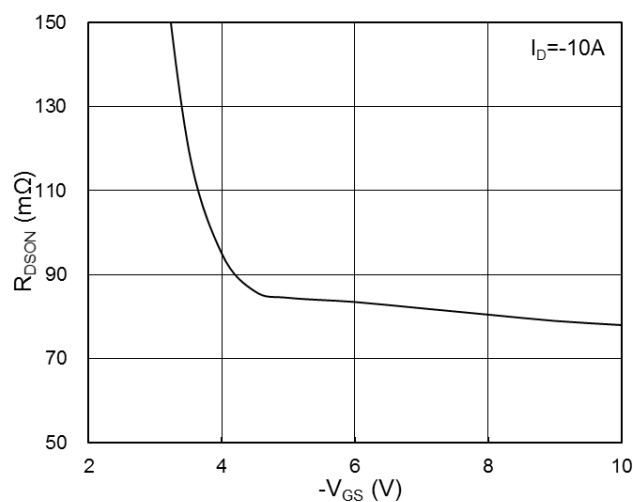


Fig.2 On-Resistance vs G-S Voltage

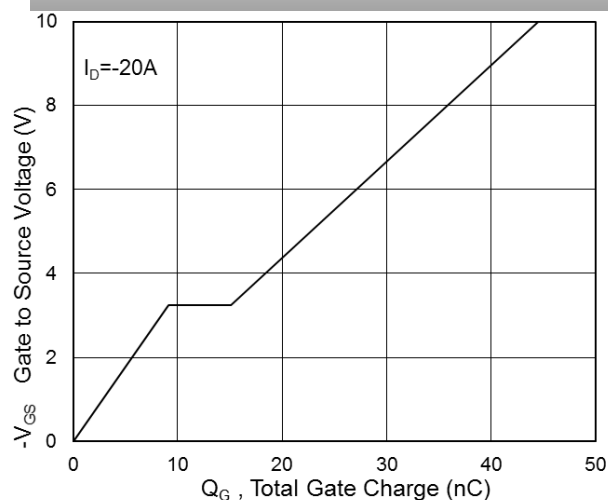


Fig.4 Gate-Charge Characteristics

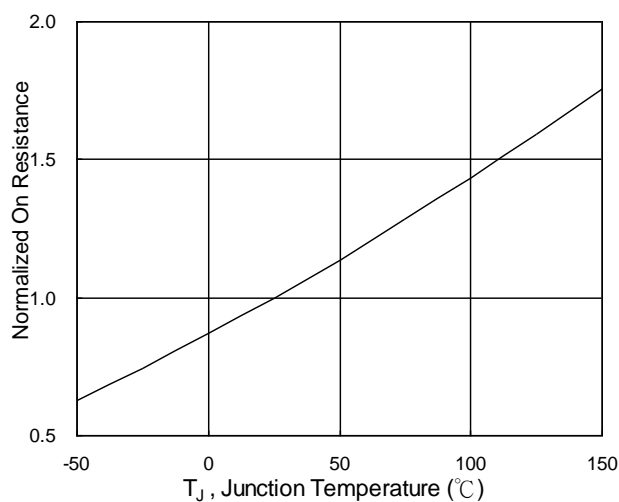
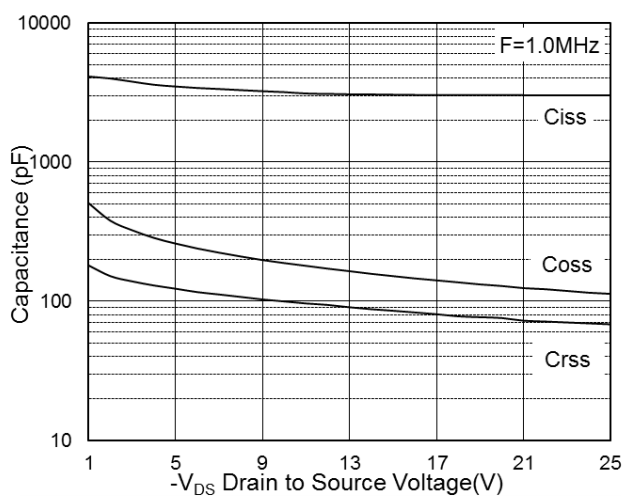
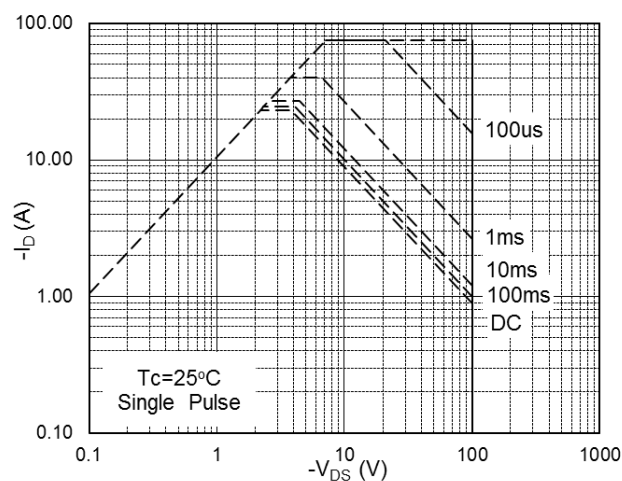
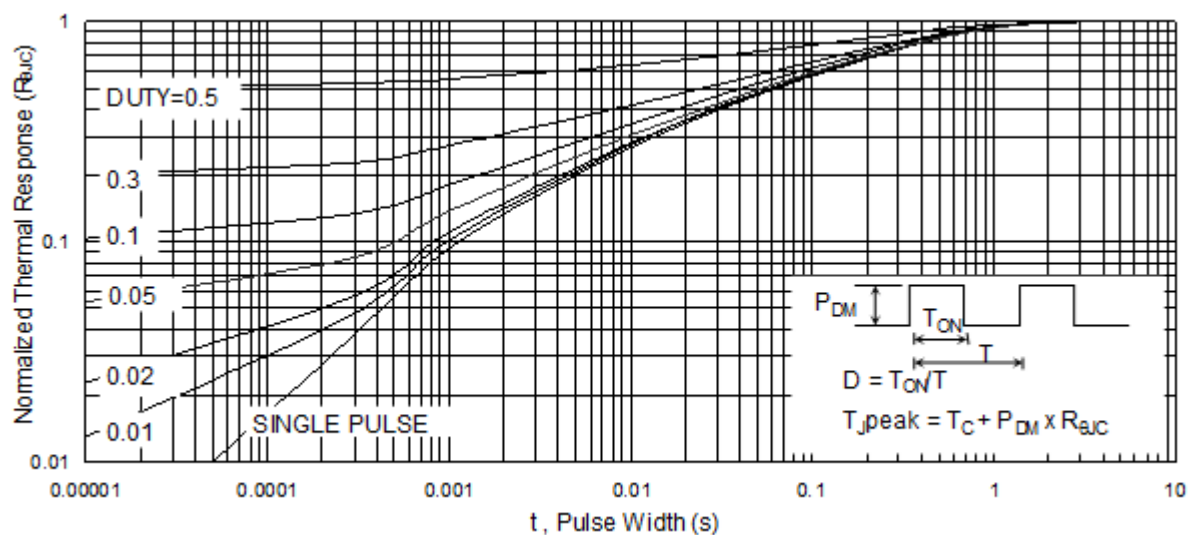
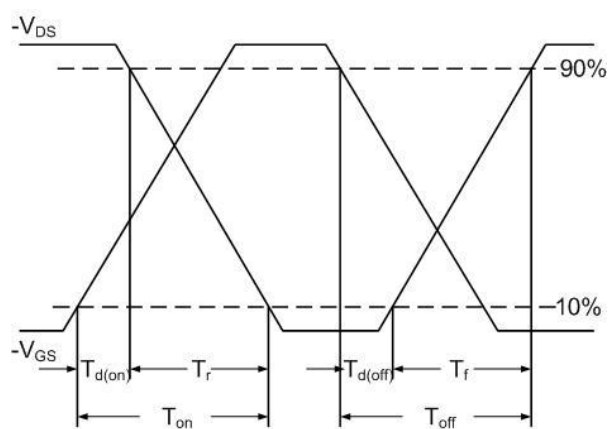
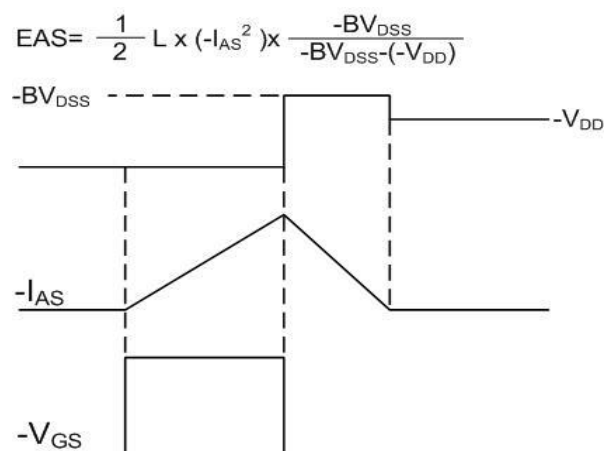


Fig.6 Normalized $R_{DS(on)}$ vs T_J

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Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform

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